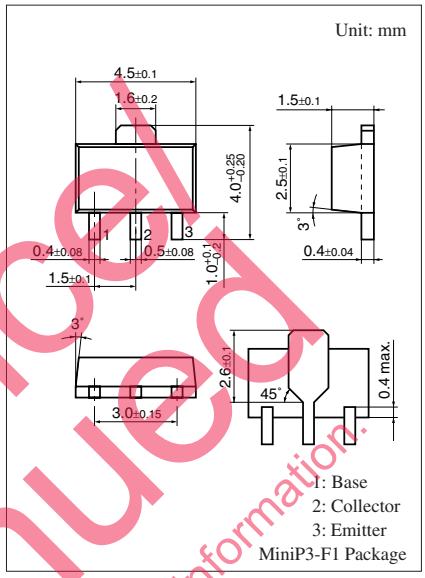
2SC5026

Silicon NPN epitaxial planar type

For low-frequency output amplification
Complementary to 2SA1890



Marking Symbol: 2A

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High collector-emitter voltage (Base open) V_{CEO}
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	80	V
Collector-emitter voltage (Base open)	V_{CEO}	80	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	1	A
Peak collector current	I_{CP}	1.5	A
Collector power dissipation *	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note) *: Copper plate at the collector is more than 1 cm^2 in area, 1.7 mm in thickness
Absolute maximum rating without heat sink for P_C is 0.5 W

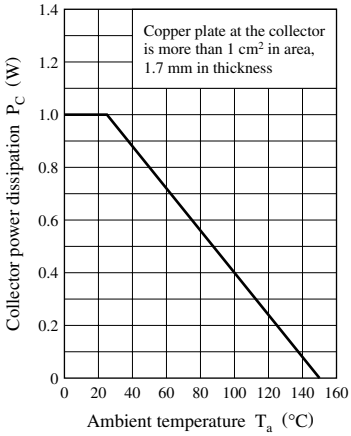
■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	I_C = 10 µA, I_E = 0	80			V
Collector-emitter voltage (Base open)	V_{CEO}	I_C = 1 mA, I_B = 0	80			V
Emitter-base voltage (Collector open)	V_{EBO}	I_E = 10 µA, I_C = 0	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	V_{CB} = 40 V, I_E = 0			0.1	µA
Forward current transfer ratio	h_{FE1} *2	V_{CE} = 2 V, I_C = 100 mA	120		340	—
	h_{FE2} *1	V_{CE} = 2 V, I_C = 500 mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 500 mA, I_B = 50 mA		0.15	0.3	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	I_C = 500 mA, I_B = 50 mA		0.85	1.2	V
Transition frequency	f_T	V_{CB} = 10 V, I_E = −50 mA, f = 200 MHz		120		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz		10	20	pF

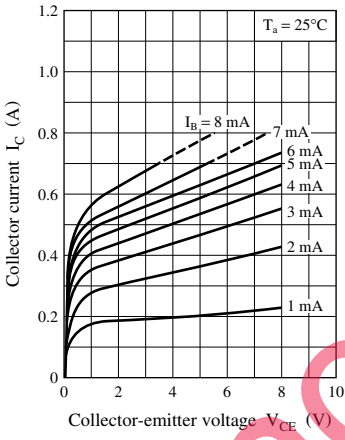
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *1: Pulse measurement
*2: Rank classification

Rank	R	S
h_{FE1}	120 to 240	170 to 340

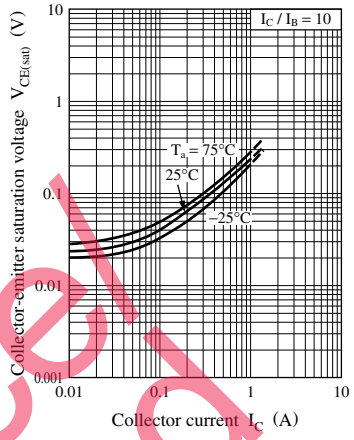
P_C — T_a



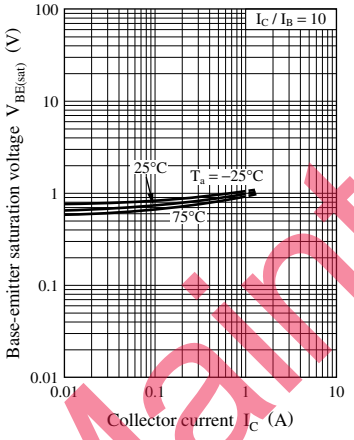
I_C — V_{CE}



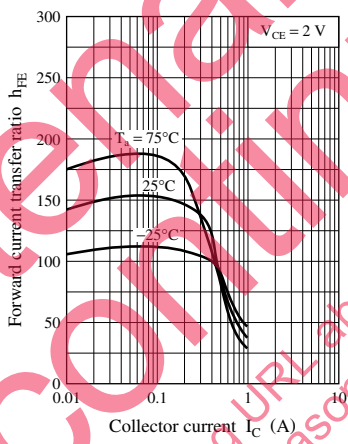
$V_{CE(sat)}$ — I_C



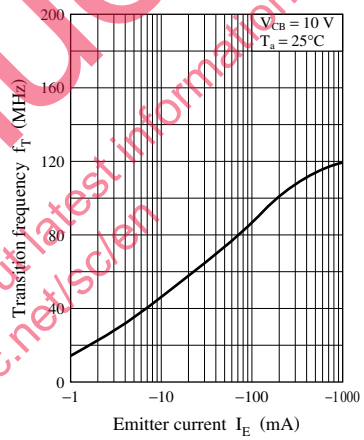
$V_{BE(sat)}$ — I_C



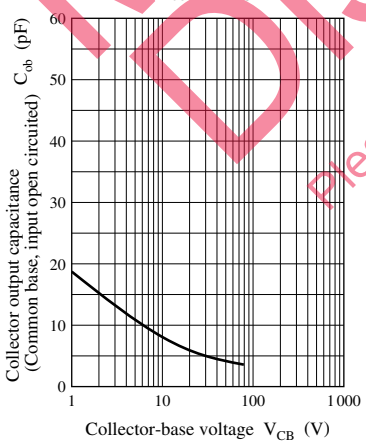
h_{FE} — I_C



f_T — I_E



C_{ob} — V_{CB}



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